Form PTO 1449 (Modified)

U.S DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO. 212020US99 SERIAL NO. 09/911,444

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APPLICANT Tomasz KLOSOWIAK, et al. GROUP

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		DOCUMENT.	DATE	U.S. PATENT DOCUMEN NAME	CLA	SS	SUB CLASS	FILING DATE IF APPROPRIATE
XAMINER INITIAL		DOCUMENT NUMBER					LLASS	11 74 113
1 INTERIOR	AA 3,	802,967	04/09/74	Ladany et al.			 	
17	AB 4	174,422	11/13/79	Matthews et al.		1-	 	
	AC 4	,404,265	09/13/83	Manasevit		╁	 	
	AD 4	,482,906	11/13/84	Hovel et al.		\vdash	 	+
-+-	AE 4	,523,211	06/11/85	Morimoto et al.		├	┼╌┼╴	+
	AF 4	,661,176	04/28/87	Manasevit			+	
	AG A	,793,872	12/27/88	Meunier et al.		-	+	
	AH P	,846,926	07/11/89	Kay et al.		 	} {-	
	LAJ L	1,855,249	08/08/89	Akasaki et al.		+-	┼┼-	
	1 1	4,891,091	01/02/90	Shastry		+	-	
	1 1	4,912,087	03/27/90	Aslam et al.		+	+-+	
	1 1	4,928,154	05/22/90	Umeno et al.		+	+	
		4,963,949	10/16/90	Wanlass et al.		_		
	· ·	5,141,894	08/25/92	Bisaro et al.		\perp	+	
	i .	5,159,413	10/27/92	Calviello et al.		\bot	+	
	I	5,173,474	12/22/92	Connell et al.		\bot	\bot	
	AQ	5,221,367	06/22/93	Chisholm et al.		\perp		
	AR	5,225,031	07/06/93	McKee et al.		\perp	\rightarrow	
		5,358,925	10/25/94	Neville Connell et al.			\perp	
	AS	5,393,352	02/28/95	Summerfelt				
	AT	5,418,216	05/23/95	Fork				
	AU	5,450,812	09/19/95					
	AV		12/26/95					
	AW	5,478,653	01/09/96					
	AX	5,482,003	05/07/96					
	AY	5,514,484	09/17/96			\top		
	AZ	5,556,463	12/31/96			1		
	BA_	5,588,995	09/23/97			\top		
	вв	5,670,798	03/31/98			1		
	ВС	5,733,641	03/31/96			\top		
	BD	5,735,949				_	_	
	BE	5,741,724	04/21/9			+		
	BF	5,810,923	09/22/9			+	-+	
	ВG	5,830,270	11/03/9			-+		
	вн	5,912,068	06/15/9			-+		
	ві	6,020,222	02/01/0			+		
1	ВЈ	6,045,626	04/04/0			$\vdash \dashv$	-+-	
1	ВК	6,064,078	05/16/0			\vdash		
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	BN	6,103,008	08/15/			+-		+ +
\- \	ВС	6,136,666	10/24/			+-		+
ļ -	BP	6,174,755	01/16/			┼		+
	J. BC	6,180,486	01/30/	/01 Leobandung et al.				<u> </u>

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AMINER		DOCUMENT	DATE		NAME	CLA	SS	SUE	ss	IF APPROPRIATE
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71. 1.	J		02/08/77	Andringa						
<u></u>		4,006,989 4,284,329	08/18/81	Smith et al.						
		4,777,613	10/11/98	Shahan et al.						
		4,802,182	01/31/89	Thornton et a	al.					
	CE	4,882,300	11/21/89	Inoue et al.						
	CF	4,882,300	01/23/90	Suzuki						
	CG	4,999,842	03/12/91	Huang et al.						
	СН	5,081,062	01/14/92	Vasudev et a	al.					
	CI CJ	5,155,658	10/13/92	Inam et al.						
		5,248,564	09/28/93	Ramesh						
	CK	5,260,394	11/09/93	Tazaki et al.				<u> </u>		
	CM	5,270,298	12/14/93	Ramesh						
		5,286,985	02/15/94	Taddiken						
	CN	5,310,707	05/10/94	Oishi et al.					\	
	CP CP	5,326,721	07/05/94	Summerfelt					1	
{_	CQ	5,404,581	04/04/95	Honjo			1		 	
	CR	5,418,389	05/23/95	Watanabe			\perp			
\longrightarrow	cs	5,436,759	07/25/95	Dijaii et al.			<u>_</u>		_	
{	CT	5,576,879	11/19/96	Nashimoto			1_	 _		
}_	CU	5.606,184	02/25/97	Abrokwah,	et al.			\perp		
	CV	5,640,267	06/17/97	May et al.			↓		}	
	cw		10/07/97	Hayashi et	al.				+-	
	CX	5,729,641	03/17/98	Chandonn	et et al.					
	CY		08/04/98	Но			↓			
	CZ		10/20/98	Ho et al.			1_		}_	
	DA		01/05/99	Beranek e	et al.					
	DB		02/23/99	Brunel et	al.		_	_	-	
	DC		07/20/9							
	DD		08/10/9	9 Abrokwah	n, et al.		_			ļ
	DE		11/09/9	9 Lo			\rightarrow			
	DF		11/23/9	1			\rightarrow			
	DC		12/14/9	9 Corman e	et al.		<u>- \</u>			
	DH		12/28/9	1				-+-	-	
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	D.		08/22/0	1						
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-		N 6,128,178	10/03/				\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \			
		0 6,143,072	11/07/	00 McKee	et al.				+	
		P 6,184,144	02/06/	01 Lo			1		\rightarrow	

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IITIAL	1	NUMBER	11/20/84	Hawrylo		1	
11. 0.		4,484,332		Scifres et al.		1	
1		4,815,084	155.2	Eshita et al.			
	EC	4,876,219	10/2 1/00	Umeno et al.		1-7	
	ED	4,963,508	10/22/91	Abrokwah, et al.			
	EE	5,060,031	11/05/91	Mooney et al.			
	EF	5,063,166	05/26/92	Lebby et al.			
	EG	5,116,461	06/30/92	Delcoco et al.			
	EH	5,127,067	09/01/92	Ma			
	EI	5,144,409	03/08/94	Chapple-Sokol et al		11	
	EJ	5,293,050	10/18/94	Calviello et al.		11	
	EK	5,356,831	02/21/95	Kao et al.		1	
	EL	5,391,515	08/15/95	Ma		1	
	EM	5,442,191	08/22/95	Abrokwah, et al.			
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	EO	5,480,829	06/18/96	Oakley			
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	FC		05/02/00	Pan			
	FD		10/24/00				
1	FE		11/14/00				
	FO		01/16/01				
1	FF		01/30/01				
\longrightarrow	FI		12/30/0	Lehovec		<u> </u>	
-	FJ		08/16/83	Pitt et al.			
-	F		01/03/84			}	
-	- FI		10/24/			/-	1
		M 4,482,422	11/84	McGinn et al.			
+		N 4,667,088	05/19/8	7 Kramer			
 		O 4,772,929	09/20/8				<u>`</u>
		P 4,841,775	06/27/8				
<i>\</i>		Q 4,845,044	07/04/8			}	\ \

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ATTY DOCKET NO. 212020US99 SERIAL NO. 09/911,444

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	y 1	DOCUMENT	DATE		NAME				CLASS	3	IF APPROPRIATE
AMAL	2	NUMBER 1 969 376	09/19/89	Lessi	n et al.			\perp			
1 de		4,868,376 4,885,376	12/05/89	Verk	ade		\bot		-	+	
7	<u> </u>	4,888,202	12/89	Mura	kami et al.			\perp		_	
	1-	4,891,091	12/90	Wan	lass et al.			_	\rightarrow		
		5,051,790	09/24/91	Ham	mer			\perp	4		
	GE		10/08/91	Belt	et al.						
	GF	5,055,445	11/14/92	Nist	imura et al.						
	GG	5,081,519	09/01/92	Pirr	ıng et al.						
	GH	5,143,854	02/09/93		hnaswamy et al.				_	\perp	
	GI	5,185,589	03/02/93	- 1	stavsson						
	G١	5,191,625	03/16/93		ok et al.					\perp	
	GK	5,194,397	05/04/93	1 _	ayan et al.						
	GL	5,208,182	06/01/93	- 1	ger et al.					\rightarrow	
	GM	5,216,729	05/24/94		remans et al.						
	GN	5,314,547	10/04/94		drews						
	GO	5,352,926	10/18/94	- 1	rranova et al.						
	GP	5,356,509	12/06/94		scher						
	GQ	5,371,734			zaki et al.						
	GR	5,372,992	12/94		amagata et al.			\top			
	GS	5,405,802	04/11/95		oshizawa et al.			1			
	GT	5,442,561	08/15/95		hibasaki et al.		17		1	-	
1	GU		09/26/95		hikawa et al.		1	\vdash		`\	
	GV		11/14/95				+-	1		1	
	G۷		12/05/95	·	hi ummerfelt		+	1	1		
1	GX		12/95				+-	1	+		
-	GY		12/26/9		aca et al.		+-	+	+		
-	GZ	5,486,406	01/23/9		Shi		+-	+	+-		
-	HA	5,491,461	02/13/9	-	Partin et al.		+	+-	+		
 +	HE	5,492,859	02/20/9		Sakaguchi et al.		+	+-	+-	:	1
 	- Н	5,494,711	02/27/9		Takeda et al.		+	+	+	1	
-	HI	5,504,035	04/02/9		Rostoker et al.		-	1-		+	
1	— н	E 5,504,183	04/02/9		Shi		+	+-		+	
-	— Н	F 5,511,238	04/23/9		Bayraktaroglu		-	+			
 		G 5,512,773	04/96		Wolf et al.			+	+		+
 		H 5,515,047	05/07/	96	Yamakido et al.			+			
 			05/14/	96	Yamashita et al.			+	-+-		
\		J 5,519,235	05/96		Ramesh			+			
ļ	\	1K 5,549,977	08/96		Jin et al.		\dashv	-			
 		1L 5,551,238	09/03	/96	Prueitt						
ļ		HM 5,552,547	09/03	/96	Shi		_	- 7			
		HN 5,589,284	12/31	/96	Summerfelt et al.						
ļ		HO 5,602,418	02/11	/97	lmai et al.						
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1. 1	KA	6,153,		02/01	1	a et al					
1	KB	6,191		03/20/01	Ella		T -				
7	KC	6,204		05/01/01	Yi et	al.					
	KD	6,224		05/01/01		yama et al.				T_	
	KE	6,225		05/01/01	Yu e			1			
	KF	6,241			1	tner et al.		1			
	KG	6,265		07/24/01		cke et al.	+				
	кн	1	3,486	11/01		zuki et al.	-	1	1	\top	
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	KJ		2/0008234	01/02	1	awaga et al.	+	\dagger	T		
	KK	1	0,213	06/13/72	i	reshi et al.		1	1	1	
	KL	1	6,007	07/05/88	1	nsperger et al.		+	+	1	
	KM	4,77	73,063	09/20/88				+	+-	1	
	KN	1	94,489	02/28/95		hrgardt et al.	-	+	+	+	
	ко		06,202	04/11/95			\dashv	+	+	\top	
	KP	5,5	28,067	06/18/96		rb et al.	-+	+	\top	\top	
	ΚQ	1.	72,052	11/05/96		shihara et al.		+	+	_	
	KR	5,7	67,543	06/16/98		oms et al.		+	+	+	
	KS	6,1	75,497	01/16/0		seng et al.		\dashv	+	-	
	KT	6,1	197,503	03/06/0		o-Dinh et al.		+	\dashv	1	
	ΚŪ	6,2	248,459	06/19/0		ang et al.		-+	\dashv	+	
 	KV	6,2	252,261	06/26/0		sui et al.			\dashv	+	
 	KV	v 6,	255,198	07/03/0		inthicum et al.	-+		-+	+-	
 	k	6,	268,269	07/31/0		ee et al.				+	
├ ── 	K		291,319	09/18/0		'u et al.			-+	+	
 		z 6,	316,785	11/13/0		lunoue et al.		+		+	
-	L/	6	,343,171	01/29/		oshimura et al.		\dashv		+	
1	LE	3 4	,965,649	10/23/		Zanio et al.				\longrightarrow	
-		c 6	,253,649	05/01	1	Kawahara et al.				-+	
├	L	D 6	,211,096	04/01		Allman et al.		 -		-+	
1		E 6	5,239,449	05/29/		Fafard et al.		+-		++	
 (F	2001/0013313	08/16	01	Droopad et al.		+-}		 	
 			6,184,044	02/06		Sone et al.		+-+		-	
1		- 1	6,011,646	01/04	/00	Mirkarimi et al.		1-1		+-1	
		1	5,227,196	07/13	/93	ltoh		+		1-1	-
 		1	6,150,239	11/21	/00	Goesele et al.		+-1		┼	
 			5,441,577	08/15	/95	Sasaki et al.		+		+	+
1			4,459,325	07/10)/84	Nozawa et al.		+-4		+-	
	}		4,392,297	07/1	2/83	Little		-	}	-	1-1
			4,289,920	09/1	5/81	Hovel		-	-	+-	+
	 	LO	5,281,834	01/2	5/94	Cambou et al.		4	 	-	1
 	-	LP	4,901,133	02/1	3/90	Curran et al.			1	-	+
	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	LQ	5,514,904	05/0	7/96	Onga et al.		1			<u>!l</u>

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE Form PIO 1449

ATTY DOCKET NO. 212020US99 APPLICANT

SERIAL NO.

09/911,444

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AMINER	-	DC	OCUMENT NUMBER	DATE		NAME	CLAS	ss	CLA		IF APPROPRIATE
	MA	5,553,0		09/03/96		eki et al.	++	-		+	
1	MA	5,533,0		06/18/96	3 Ya	anagase et al.	+++			+	
-	MB	6,229,1		05/08/01		uzuki	-+	+-+	 	+-+	
+	MC	4,748,4		05/31/88	8 Va	asudev	-+	+-1	-	+-1	+
	┼	4,748,2		01/08/91	1 Vi	inal		+-	+	+-1	+
-+	ME	5,754,		05/19/98	18 V.	an De Voorde et al.	-+-	+-	+-	+	
	+	+		08/22/00		'ano		+	+-	+-	
	MG	+		12/17/9	71 G	Giles et al.		+	+-	+	
-+-	MH	+		08/18/9		Soref et al.		+-	+-	+-	
	MJ			03/11/9		Ho et al.		+	+-	+	+
	MK			03/26/0		Manabe et al.		+	+	+-	
			2,686	06/05/0		Kishimoto et al.		+-	+	+-	
	ML		39,123	11/18/9		Major et al.		+-	+-	+-	
	MM		70,800	09/23/		Nakao et al.		+	+	+	+
	MN		67,809	11/26/		Tsubota		+	+	+	+
	MC		96,205	01/21/	-	Reedy et al.		+	+	+	
			75,555	01/16/	₹/01	Hoole		-	+	+	
	MC		357,122	10/18	+	Okubora et al.		+-	+	+	
	MF	-+)84,130	04/11		Holton		+	+	+	
	MS MS		093,302	07/25	5/00	Montgomery		+	+	+	-
			372,813	04/16		Johnson et al.		+	+	+	
			608,046	03/04		Cook et al.		+	+	+	
			955,591	09/2	21/99	Imbach et al.		+	+	+	
			022,963	02/0	08/00	McGall et al.		+	-+	+	
 			,083,697	07/C	04/00	Beecher et al.		+	\rightarrow	-	
 			,063,081	11/C	05/91	Cozzette et al.	+	+	-+		
╟ ┼			,479,317	12/2	/26/95	Ramesh		+		'	+
 			,306,649	04/2	/26/94	Hebert		+			-
			5,962,069	10/0	/05/99	Schindler et al.		+		 	-
			5,541,422		/30/96			<u>'</u>		 	++
-			5,873,977		2/23/99			4		+	+-
			5,538,941		7/23/96	-1 -1 -1		\longrightarrow	<u> </u>	+-1	+
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Form PTO 1449

U.S. DEPARTMENT OF COMMERCE
(Modified)

PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

212020US99

OP/911,444

APPLICANT

Tomasz KLOSOWIAK, et al.

FILING DATE

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	+-	Oì	+	72,356 B1	04/16/02	-	ornton et al.	+	+	+	1	
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	-+			5,886,867	03/23		Chivukula et al.		+-	+	-	
	+			5,028,976	07/02		Ozaki et al.		+-	+-	++	
	-+			5,869,845	02/09		Vander Wagt et al.		+-	+-	+	
	+	+		5,596,214	01/21	1/97	Endo		+-	+-	+-	
	-+			6,391,674 B2	05/21	1/02	Ziegler		+	+-	+	
	-+			6,275,122 B1	08/14	4/01	Speidell et al.		+-	+-	++	
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-	+		·	6,210,988 B1	04/0	03/01	Howe et al.		+	+-	+	
-	-+			6,392,257	05/2	21/02	Ramdani et al.		+	+-	+	
-		—	PF PG	4,442,590	04/1	17/84	Stockton et al.		+	+	+	
-			PH	5,603,764	02/	18/97	Matsuda et al.		+	+	+	
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Form PTO 1449

U.S. DEPARTMENT OF COMMERCE
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JULY DOCKET NO.

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Tomasz KLOSOWIAK, et al.

FILING DATE

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100		5,569,953	10/29/96		awa et al.		+	+	1	<u> </u>	
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1-1		6,248,621 B1	06/19/01	Wilk			+	+	+	1	
+-		5,266,355	11/30/93		nberg et al.		-+	+	+	1	
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+-		6,039,803	03/21/00		gerald et al.			+	+	1	
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+	QI	5,420,102	05/30/95		shavardhan et al.	+		+	+	_	
+	Ø1	5,210,763	05/11/93		vis et al.		+	+		<u></u>	
-	QK	5,103,494	04/07/92	-+				+	+		
-	QL	4,594,000	06/10/86		k et al.		+	-+	+		
-+-	QM	4,297,656	10/27/81				+	-+	-+		
-+-	QN	5,244,818	09/14/93		kers et al.		+	+			
+	QO	2010 754	04/11/00	<u> </u>	Asaro et al		+				
-	QP		01/16/96		tahara et al.		+-+				
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	QY	Y 6,306,668 B1	10/23/		McKee et al.		+	+-			
	QZ	Z 6,143,366	11/07/		_U		+	+	1		
	R/	RA 6,410,941	06/25/		Taylor et al.		+	+	1		
	R	7.007.409	03/14/		Stoner et al.		+	+	1	-	
-+		RC 6,432,546 B1	08/13		Ramesh et al.		+	+	14		
+		RD 6,345,424	02/12		Hasegawa et al.		+	+	+	1	
		RE 6,338,756 B2	01/15		Dietze		+	+	+	1	
		RF 5,516,725	05/14		Chang et al.		+	+	+		
		RG 4,667,212	05/19		Nakamura		+	+	+	+ 1	
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		RI 3,914,137			Huffman et al.		+	+	+	7	
+	-+	RJ 5,753,928		19/98	Krause		+	+	+	7	
		RK 5,977,567)2/99	Verdiell		+	+	+	- 1	
		RL 5,130,762		14/92	Kulick		+	+	+		
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+		RO 5,163,118	11/	10/92	Lorenzo et al.		-+	-+	+	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
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9, (N		6,156,581	12,00,11	Vaudo et al.	+-	 	
1	() 		5,395,663	-	Tabata et al.	-+-	 	
-+	\rightarrow		4,146,297		Alferness et al.		+-+	
+			5,452,118		Maruska		+	
+			5,889,296		Imamura et al.		1-1-	
+		SF	6,300,615 B1		Shinohara et al.		1-1-	
		SG	6,232,910 B1	05/15/01	Bell et al.		11	
		SH	5,686,741	11/11/97	Ohori et al.		1	
	\prod	SI	4,959,702	09/25/90	Moyer et al			
	I	SJ	6,100,578	08/08/00	Suzuki			
		sĸ	6,410,947 B1	06/25/02	Wada			
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		SM	6,461,927 B1	10/08/02	Higgins, Jr. et al.		1	
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		1	TG 6,393,167 B1	05/21/0				
		\Box	TH 5,760,427	06/02/9				
		+	TI 6,411,756 B2	06/25/				
			TJ 5,668,048	09/16/			117	
	$\overline{\perp}$	-+	TK 5,852,687	06/16/			1	1
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Tomasz KLOSOWIAK, et al. GROUP

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1.7	\ UA	5,635,433		Sengupta Sengupta et al.			1	
1	UB	5,427,988		Koizumi et al.		\prod	17	
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